



#4/H
7/16/02
L. Dwyer

In re application of

JOZEF D. MITROS

Serial No. 10/020,034 (TI-32931)

Filed December 7, 2001

For: METHODS FOR FABRICATING LOW CHC
DEGRADATION MOSFET TRANSISTORS

Art Unit 2823

Examiner Long Pham

Commissioner for Patents
Washington, D. C. 20231

Sir:

AMENDMENT UNDER 37 C.F.R. 1.111

In response to the Office action dated May 30, 2002, please amend the above-identified application as follows:

In the claims:

Amend claim 1 as follows:

device, comprising the steps of:

providing a semiconductor device substrate;

implanting a first transistor region associated with a first transistor device in the semiconductor device substrate [using a first implantation process] to adjust a threshold voltage associated with the first transistor device[,] and concurrently implanting a portion